



# GSF31012

## FAST RECOVERY STUD DIODE

UL-certified insulating sleeve

<b>VOLTAGE UP TO</b>	<b>1200 V</b>
<b>AVERAGE CURRENT</b>	<b>125 A</b>
<b>SURGE CURRENT</b>	<b>2.8 kA</b>

### BLOCKING CHARACTERISTICS

Characteristic		Conditions	Value
V <sub>RRM</sub>	Repetitive peak reverse voltage		1200 V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage		1300 V
I <sub>RRM</sub>	Repetitive peak reverse current, max.	V <sub>RRM</sub> , single phase, half wave, T <sub>j</sub> = T <sub>jmax</sub>	35 mA

### FORWARD CHARACTERISTICS

I <sub>F(AV)</sub>	Average forward current	Sine wave, 180° conduction, T <sub>h</sub> = 100 °C	125 A
I <sub>F(RMS)</sub>	R.M.S. forward current	Sine wave, 180° conduction, T <sub>h</sub> = 100 °C	196 A
I <sub>F(SM)</sub>	Surge forward current	Non rep. half sine wave, 50 Hz, V <sub>R</sub> = 0 V, T <sub>j</sub> = T <sub>jmax</sub>	2.8 kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination		39 kA <sup>2</sup> s
V <sub>F(TO)</sub>	Threshold voltage	T <sub>j</sub> = T <sub>jmax</sub>	1.2 V
r <sub>F</sub>	Forward slope resistance	T <sub>j</sub> = T <sub>jmax</sub>	2.3 mΩ
V <sub>FM</sub>	Peak forward voltage, max	Forward current I <sub>F</sub> = 450 A, T <sub>j</sub> = 25°C	2.5 V

### SWITCHING CHARACTERISTICS

t <sub>rr</sub>	Reverse recovery time, typ	T <sub>j</sub> = 125 °C , I <sub>F</sub> = 350 A, di/dt = -25 A/μs V <sub>R</sub> =30 V	1 μs
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### THERMAL AND MECHANICAL CHARACTERISTICS

R <sub>th(j-c)</sub>	Thermal resistance (junction to case)	Double side cooled	0.25 °C/W
R <sub>th(c-h)</sub>	Thermal resistance (case to heatsink)	Double side cooled	0.08 °C/W
T <sub>jmax</sub>	Max operating junction temperature		150 °C
T <sub>stg</sub>	Storage temperature		-40 / 150 °C
M	Mounting torque		10 N·m
	Mass		100 g

### Ordering information

cathode on stud	anode on stud		
GSF31012-vvtt	GSFR31012-vvtt	v <sub>v</sub> =V <sub>RRM</sub> /100	t <sub>t</sub> = t <sub>rr</sub> [μs] * 10
example	GSF31012-1210	1200 V	1 μs @ 25°C